

# ON Semiconductor

## Is Now



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# NVATS5A107PLZ

## Power MOSFET

–40 V, 17 mΩ, –55 A, P-Channel

Automotive Power MOSFET designed for compact and efficient designs and including high thermal performance.

AEC-Q101 qualified MOSFET and PPAP capable suitable for automotive applications.

### Features

- Low On-Resistance
- High Current Capability
- 100% Avalanche Tested
- AEC-Q101 qualified and PPAP capable
- ATPAK package is pin-compatible with DPAK (TO-252)
- Pb-Free, Halogen Free and RoHS compliance

### Typical Applications

- Reverse Battery Protection
- Load Switch
- Automotive Front Lighting
- Automotive Body Controllers

### SPECIFICATIONS

**ABSOLUTE MAXIMUM RATING** at  $T_a = 25^\circ\text{C}$  (Note 1)

| Parameter                                                                 | Symbol         | Value       | Unit             |
|---------------------------------------------------------------------------|----------------|-------------|------------------|
| Drain to Source Voltage                                                   | $V_{DS}$       | –40         | V                |
| Gate to Source Voltage                                                    | $V_{GS}$       | $\pm 20$    | V                |
| Drain Current (DC)                                                        | $I_D$          | –55         | A                |
| Drain Current (Pulse)<br>$PW \leq 10 \mu\text{s}$ , duty cycle $\leq 1\%$ | $I_{DP}$       | –165        | A                |
| Power Dissipation<br>$T_c = 25^\circ\text{C}$                             | $P_D$          | 60          | W                |
| Operating Junction and<br>Storage Temperature                             | $T_j, T_{stg}$ | –55 to +175 | $^\circ\text{C}$ |
| Avalanche Energy (Single Pulse) (Note 2)                                  | $E_{AS}$       | 80          | mJ               |
| Avalanche Current (Note 3)                                                | $I_{AV}$       | –25         | A                |

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2 :  $V_{DD} = -10 \text{ V}$ ,  $L = 200 \mu\text{H}$ ,  $I_{AV} = -25 \text{ A}$

3 :  $L \leq 200 \mu\text{H}$ , Single pulse

### THERMAL RESISTANCE RATINGS

| Parameter                                                  | Symbol          | Value | Unit               |
|------------------------------------------------------------|-----------------|-------|--------------------|
| Junction to Case Steady State ( $T_c = 25^\circ\text{C}$ ) | $R_{\theta JC}$ | 2.5   | $^\circ\text{C/W}$ |
| Junction to Ambient (Note 4)                               | $R_{\theta JA}$ | 80.1  | $^\circ\text{C/W}$ |

Note 4 : Surface mounted on FR4 board using a  $130 \text{ mm}^2$ , 1 oz. Cu pad.

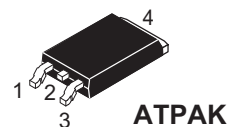
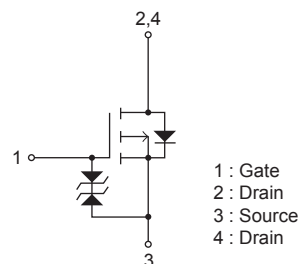


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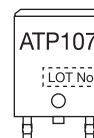
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| $V_{DS}$ | $R_{DS(on)}$ Max | $I_D$ Max |
|----------|------------------|-----------|
| –40 V    | 17 mΩ @ –10 V    | –55 A     |
|          | 26 mΩ @ –4.5 V   |           |

### ELECTRICAL CONNECTION P-Channel



### MARKING



### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

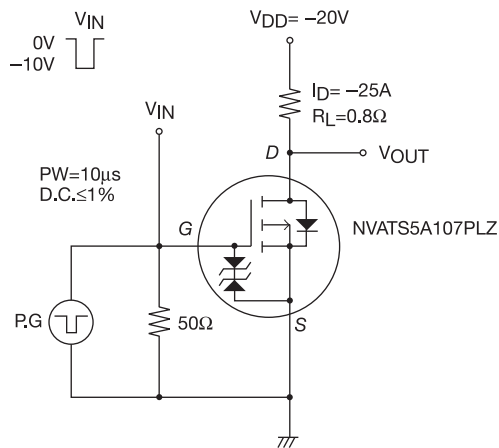
# NVATS5A107PLZ

## ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 5)

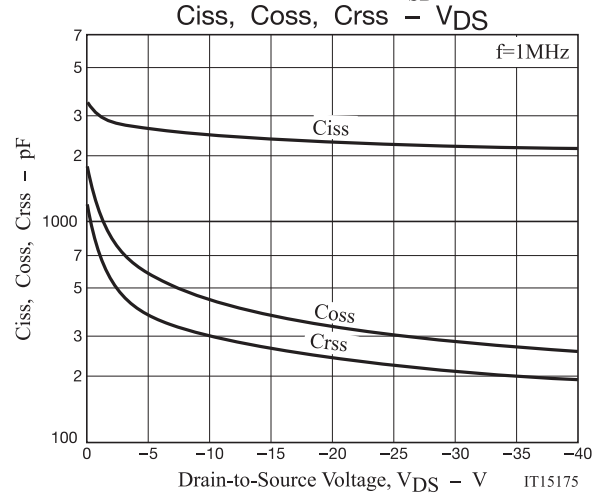
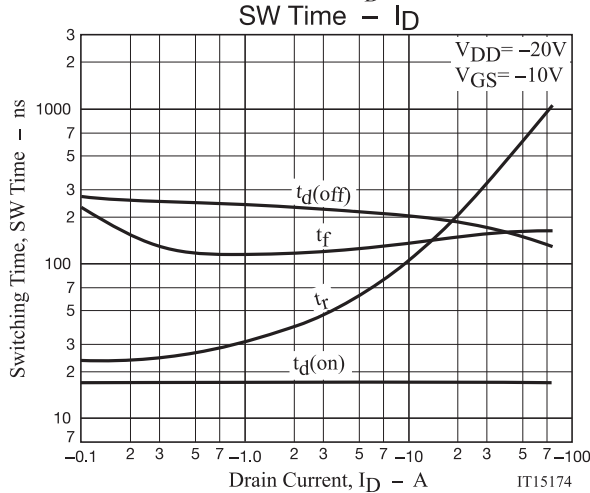
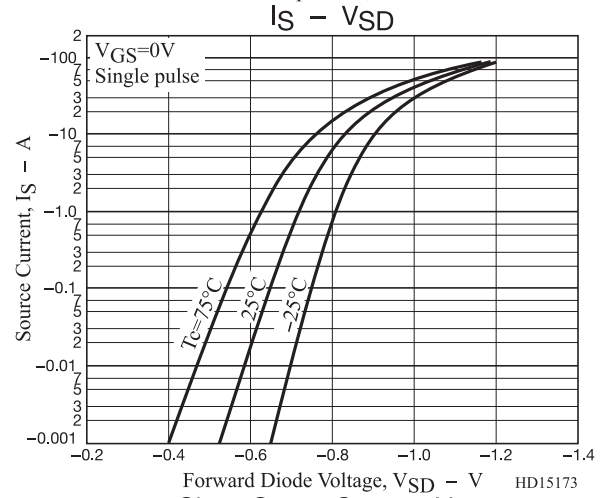
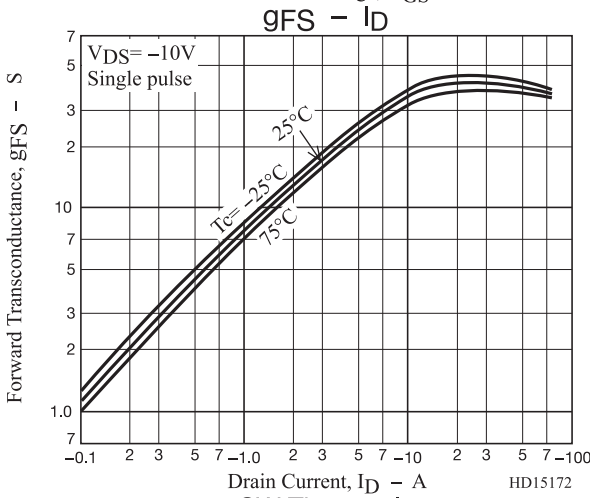
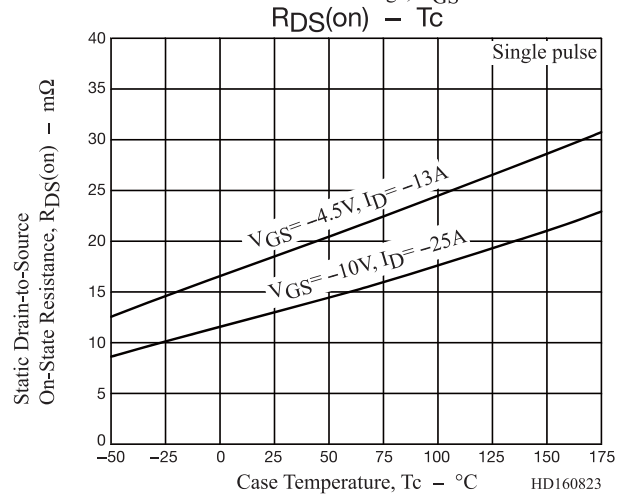
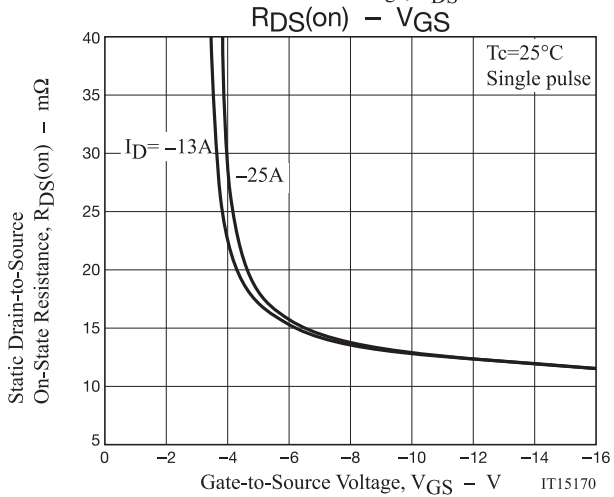
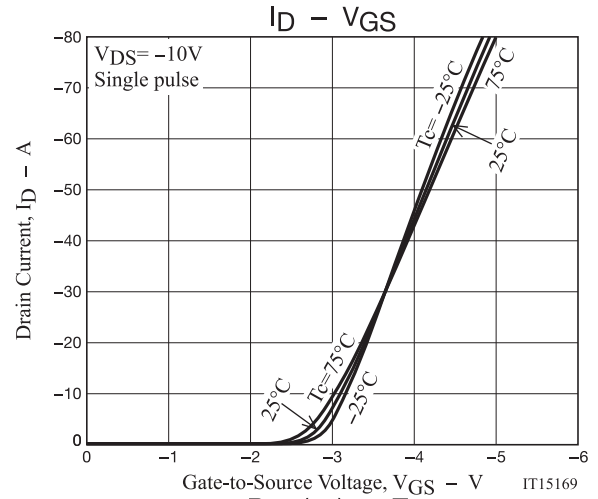
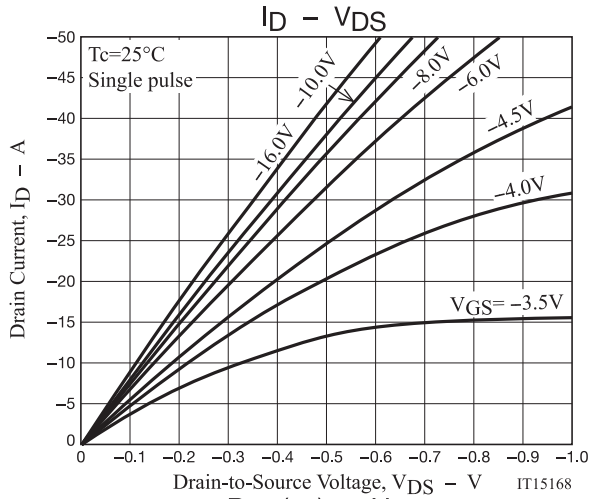
| Parameter                                  | Symbol               | Conditions                                                               | Value |       |      | Unit |
|--------------------------------------------|----------------------|--------------------------------------------------------------------------|-------|-------|------|------|
|                                            |                      |                                                                          | min   | typ   | max  |      |
| Drain to Source Breakdown Voltage          | V(BR)DSS             | I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V                            | -40   |       |      | V    |
| Zero-Gate Voltage Drain Current            | I <sub>DSS</sub>     | V <sub>DS</sub> = -40 V, V <sub>GS</sub> = 0 V                           |       |       | -1   | μA   |
| Gate to Source Leakage Current             | I <sub>GSS</sub>     | V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V                           |       |       | ±10  | μA   |
| Gate Threshold Voltage                     | V <sub>GS(th)</sub>  | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA                          | -1.2  |       | -2.6 | V    |
| Forward Transconductance                   | g <sub>FS</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -25 A                          |       | 40    |      | S    |
| Static Drain to Source On-State Resistance | R <sub>DS(on)1</sub> | I <sub>D</sub> = -25 A, V <sub>GS</sub> = -10 V                          |       | 13    | 17   | mΩ   |
|                                            | R <sub>DS(on)2</sub> | I <sub>D</sub> = -13 A, V <sub>GS</sub> = -4.5 V                         |       | 18.5  | 26   | mΩ   |
| Input Capacitance                          | C <sub>iss</sub>     | V <sub>DS</sub> = -20 V, f = 1 MHz                                       |       | 2,400 |      | pF   |
| Output Capacitance                         | C <sub>oss</sub>     |                                                                          |       | 330   |      | pF   |
| Reverse Transfer Capacitance               | C <sub>rss</sub>     |                                                                          |       | 240   |      | pF   |
| Turn-ON Delay Time                         | t <sub>d(on)</sub>   | See Fig. 1                                                               |       | 17    |      | ns   |
| Rise Time                                  | t <sub>r</sub>       |                                                                          |       | 260   |      | ns   |
| Turn-OFF Delay Time                        | t <sub>d(off)</sub>  |                                                                          |       | 190   |      | ns   |
| Fall Time                                  | t <sub>f</sub>       |                                                                          |       | 160   |      | ns   |
| Total Gate Charge                          | Q <sub>g</sub>       | V <sub>DS</sub> = -20 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -50 A |       | 47    |      | nC   |
| Gate to Source Charge                      | Q <sub>gs</sub>      |                                                                          |       | 11.5  |      | nC   |
| Gate to Drain "Miller" Charge              | Q <sub>gd</sub>      |                                                                          |       | 8     |      | nC   |
| Forward Diode Voltage                      | V <sub>SD</sub>      | I <sub>S</sub> = -50 A, V <sub>GS</sub> = 0 V                            |       | -1.02 | -1.5 | V    |

Note 5 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

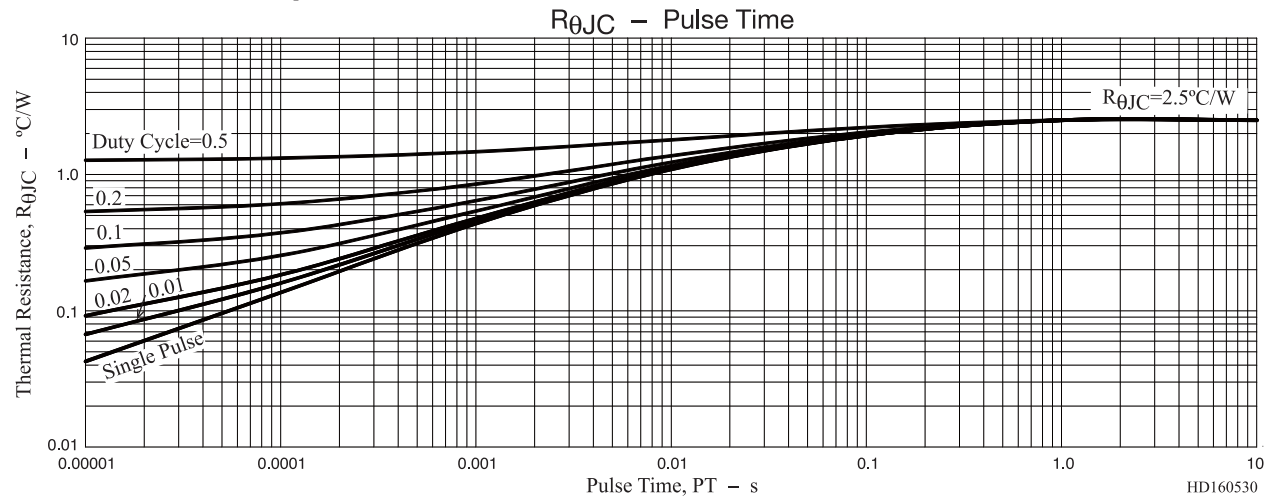
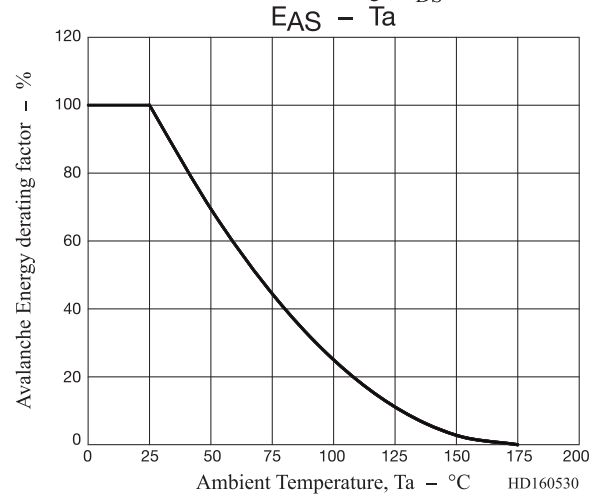
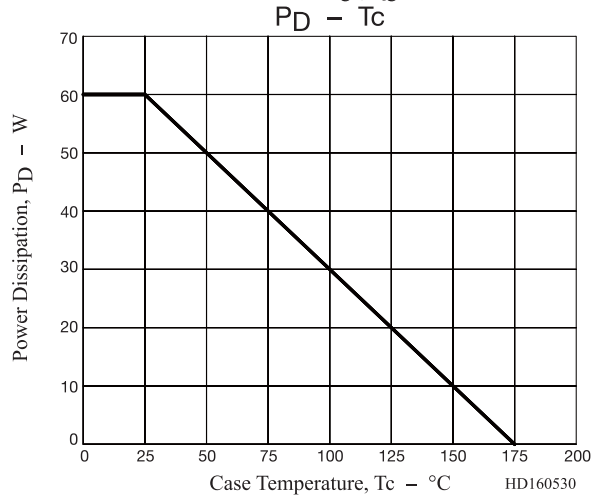
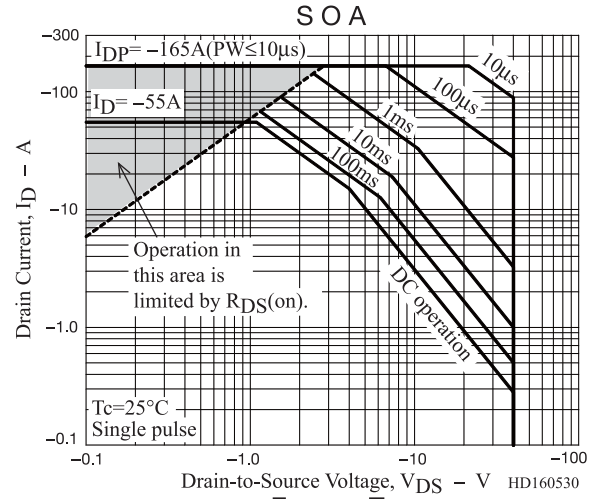
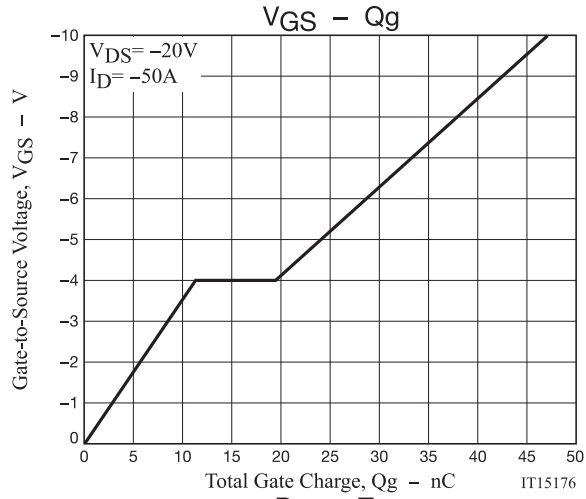
**Fig.1 Switching Time Test Circuit**



# NVATS5A107PLZ



# NVATS5A107PLZ



**NVATS5A107PLZ**

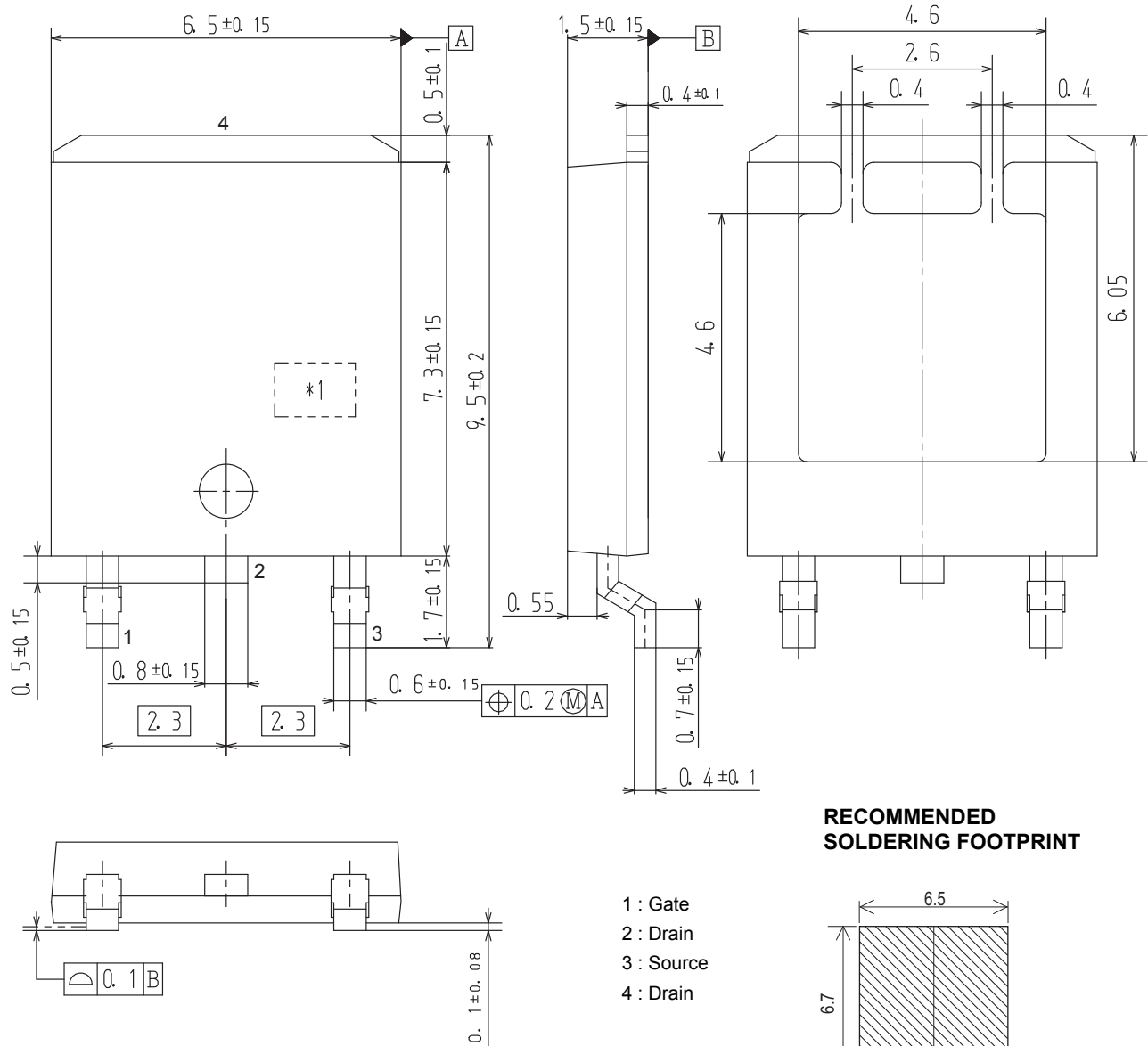
## PACKAGE DIMENSIONS

unit : mm

### DPAK (Single Gauge) / ATPAK

CASE 369AM

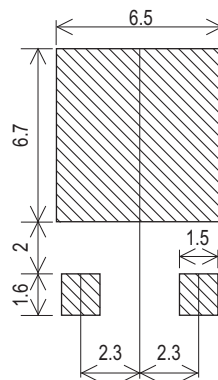
ISSUE 0



Pin2 is idle pin with electrical  
designation only carried

\*1: Lot indication

## RECOMMENDED SOLDERING FOOTPRINT



## NVATS5A107PLZ

### ORDERING INFORMATION

| Device           | Marking | Package                                                | Shipping (Qty / Packing) |
|------------------|---------|--------------------------------------------------------|--------------------------|
| NVATS5A107PLZT4G | ATP107  | DPAK(Single Gauge) / ATPAK<br>(Pb-Free / Halogen Free) | 3,000 / Tape & Reel      |

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. [http://www.onsemi.com/pub\\_link/Collateral/BRD8011-D.PDF](http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF)

Note on usage : Since the NVATS5A107PLZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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